

ABSTRACT

In a method of forming an SOI substrate, a stopper layer having an etch selectivity different from a first wafer may be formed on the first wafer having a first surface and a second surface facing each other.
5 A semiconductor layer having an etch selectivity different from the stopper layer may be formed on the stopper layer. A buried insulation layer may be formed on the semiconductor layer. The buried insulation layer may be formed by applying a compressive stress condition, to
10 have a height of a central portion of the buried insulation layer being formed higher than a height of an edge portion of the buried insulation layer.

FIG. 2

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